

HIGH-SPEED, LOW-NOISE, FULLY-DIFFERENTIAL I/O AMPLIFIERS

 Check for Samples: [THS4130](#), [THS4131](#)

FEATURES

- **High Performance**
 - 150 MHz, –3 dB Bandwidth ($V_{CC} = \pm 15\text{ V}$)
 - 51 V/ μs Slew Rate
 - –100 dB Third Harmonic Distortion at 250 kHz
- **Low Noise**
 - 1.3 nV/ $\sqrt{\text{Hz}}$ Input-Referred Noise
- **Differential-Input/Differential-Output**
 - Balanced Outputs Reject Common-Mode Noise
 - Reduced Second-Harmonic Distortion Due to Differential Output
- **Wide Power-Supply Range**
 - $V_{CC} = 5\text{ V}$ Single Supply to $\pm 15\text{ V}$ Dual Supply
- $I_{CC(SD)} = 860\ \mu\text{A}$ in Shutdown Mode (THS4130)

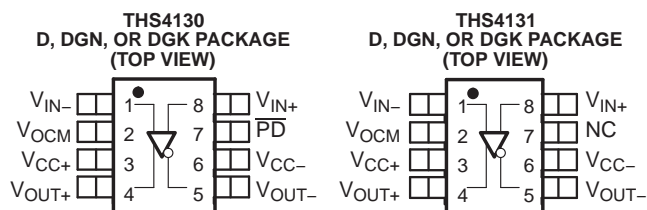
APPLICATIONS

- Single-Ended To Differential Conversion
- Differential ADC Driver
- Differential Antialiasing
- Differential Transmitter And Receiver
- Output Level Shifter

DESCRIPTION

The THS413x is one in a family of fully-differential input/differential output devices fabricated using Texas Instruments' state-of-the-art BiCom1 complementary bipolar process.

The THS413x is made of a true fully-differential signal path from input to output. This design leads to an excellent common-mode noise rejection and improved total harmonic distortion.

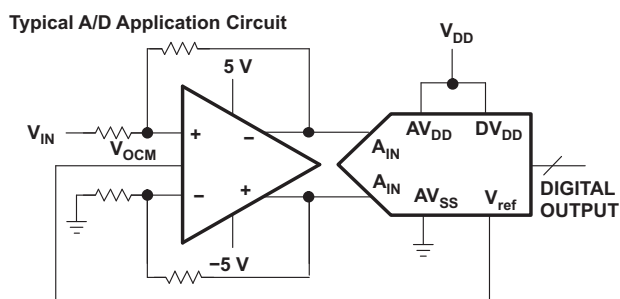


HIGH-SPEED DIFFERENTIAL I/O FAMILY

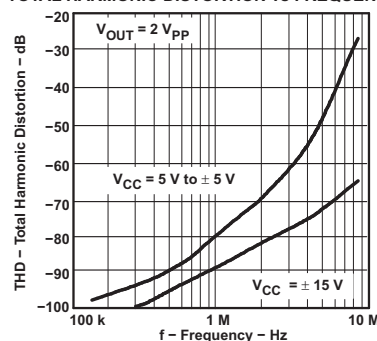
| DEVICE | NUMBER OF CHANNELS | SHUTDOWN |
|---------|--------------------|----------|
| THS4130 | 1 | X |
| THS4131 | 1 | – |

RELATED DEVICES

| DEVICE | DESCRIPTION |
|---------|--|
| THS412x | 100 MHz, 43 V/ μs , 3.7 nV/ $\sqrt{\text{Hz}}$ |
| THS414x | 160 MHz, 450 V/ μs , 6.5 nV/ $\sqrt{\text{Hz}}$ |
| THS415x | 180 MHz, 850 V/ μs , 9 nV/ $\sqrt{\text{Hz}}$ |



TOTAL HARMONIC DISTORTION vs FREQUENCY



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All other trademarks are the property of their respective owners.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

AVAILABLE OPTIONS⁽¹⁾

| T _A | PACKAGED DEVICES | | | | | EVALUATION MODULES |
|----------------|-------------------|----------------|--------|-------------|--------|--------------------|
| | SMALL OUTLINE (D) | MSOP PowerPAD™ | | MSOP | | |
| | | (DGN) | SYMBOL | (DGK) | SYMBOL | |
| 0°C to +70°C | THS4130CD | THS4130CDGN | AOB | THS4130CDGK | ATP | THS4130EVM |
| | THS4131CD | THS4131CDGN | AOD | THS4131CDGK | ATQ | THS4131EVM |
| -40°C to +85°C | THS4130ID | THS4130IDGN | AOC | THS4130IDGK | ASO | — |
| | THS4131ID | THS4131IDGN | AOE | THS4131IDGK | ASP | — |

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Over operating free-air temperature range, unless otherwise noted.

| | | UNIT | |
|--------------------------------------|---|--|----------------|
| V _{CC-} to V _{CC+} | Supply voltage | ±33 V | |
| V _I | Input voltage | ±V _{CC} | |
| I _O ⁽²⁾ | Output current | 150 mA | |
| V _{ID} | Differential input voltage | ±6 V | |
| Continuous total power dissipation | | See Dissipation Rating table | |
| T _J ⁽³⁾ | Maximum junction temperature | +150°C | |
| T _J ⁽⁴⁾ | Maximum junction temperature, continuous operation, long-term reliability | +125°C | |
| T _A | Operating free-air temperature | C-suffix | 0°C to +70°C |
| | | I-suffix | -40°C to +85°C |
| T _{STG} | Storage temperature | -65°C to +150°C | |
| ESD ratings: | | HBM | 2500 V |
| | | CDM | 1500 V |
| | | MM | 200 V |

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The THS413x may incorporate a PowerPAD on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI technical briefs [SLMA002](#) and [SLMA004](#) for more information about using the PowerPAD thermally-enhanced package.
- (3) The absolute maximum temperature under any condition is limited by the constraints of the silicon process.
- (4) The maximum junction temperature for continuous operation is limited by package constraints. Operation above this temperature may result in reduced reliability and/or lifetime of the device.

DISSIPATION RATING TABLE

| PACKAGE | θ _{JA} ⁽¹⁾ (°C/W) | θ _{JC} (°C/W) | POWER RATING ⁽²⁾ | |
|---------|---------------------------------------|------------------------|-----------------------------|------------------------|
| | | | T _A = +25°C | T _A = +85°C |
| D | 97.5 | 38.3 | 1.02 W | 410 mW |
| DGN | 58.4 | 4.7 | 1.71 W | 685 mW |
| DGK | 134 | 72 | 750 mW | 300 mW |

- (1) This data was taken using the JEDEC standard High-K test PCB.
- (2) Power rating is determined with a junction temperature of +125°C. This is the point where distortion starts to substantially increase. Thermal management of the final PCB should strive to keep the junction temperature at or below +125°C for best performance and long-term reliability.

RECOMMENDED OPERATING CONDITIONS

| | | MIN | TYP | MAX | UNIT |
|--|---------------|-----------|-----|----------|------|
| Supply voltage, V_{CC+} to V_{CC-} | Dual supply | ± 2.5 | | ± 15 | V |
| | Single supply | 5 | | 30 | |
| Operating free-air temperature, T_A | C-suffix | 0 | | +70 | °C |
| | I-suffix | -40 | | +85 | |

ELECTRICAL CHARACTERISTICS⁽¹⁾
 $V_{CC} = \pm 5$ V, $R_L = 800\ \Omega$, and $T_A = +25^\circ\text{C}$, unless otherwise noted.

| PARAMETER | | TEST CONDITIONS | | MIN | TYP | MAX | UNIT |
|----------------------------------|---|--|-------------------------------|-----|------|-----|------------------------|
| DYNAMIC PERFORMANCE | | | | | | | |
| BW | Small-signal bandwidth (-3 dB), single-ended input, differential output, $V_I = 63$ mV _{PP} | $V_{CC} = 5$ | Gain = 1, $R_f = 390\ \Omega$ | | 125 | | MHz |
| | | $V_{CC} = \pm 5$ | Gain = 1, $R_f = 390\ \Omega$ | | 135 | | |
| | | $V_{CC} = \pm 15$ | Gain = 1, $R_f = 390\ \Omega$ | | 150 | | |
| | Small-signal bandwidth (-3 dB), single-ended input, differential output, $V_I = 63$ mV _{PP} | $V_{CC} = 5$ | Gain = 2, $R_f = 750\ \Omega$ | | 80 | | |
| | | $V_{CC} = \pm 5$ | Gain = 2, $R_f = 750\ \Omega$ | | 85 | | |
| | | $V_{CC} = \pm 15$ | Gain = 2, $R_f = 750\ \Omega$ | | 90 | | |
| SR | Slew rate ⁽²⁾ | Gain = 1 | | | 52 | | V/ μ s |
| t_s | Settling time to 0.1% | Step voltage = 2 V, gain = 1 | | | 78 | | ns |
| | Settling time to 0.01% | | | | 213 | | ns |
| DISTORTION PERFORMANCE | | | | | | | |
| THD | Total harmonic distortion, differential input, differential output, gain = 1, $R_f = 390\ \Omega$, $R_L = 800\ \Omega$, $V_O = 2$ V _{PP} | $V_{CC} = 5$ | f = 250 kHz | | -95 | | dBc |
| | | | f = 1 MHz | | -81 | | |
| | | $V_{CC} = \pm 5$ | f = 250 kHz | | -96 | | |
| | | | f = 1 MHz | | -80 | | |
| | $V_{CC} = \pm 15$ | f = 250 kHz | | -97 | | | |
| | | f = 1 MHz | | -80 | | | |
| | $V_O = 4$ V _{PP} | $V_{CC} = \pm 5$ | f = 250 kHz | | -91 | | |
| | | | f = 1 MHz | | -75 | | |
| $V_{CC} = \pm 15$ | | f = 250 kHz | | -91 | | | |
| | | f = 1 MHz | | -75 | | | |
| SFDR | Spurious-free dynamic range, differential input, differential output, gain = 1, $R_f = 390\ \Omega$, $R_L = 800\ \Omega$, f = 250 kHz | $V_O = 2$ V _{PP} | $V_{CC} = \pm 2.5$ | | 97 | | dB |
| | | | $V_{CC} = \pm 5$ | | 98 | | |
| | | | $V_{CC} = \pm 15$ | | 99 | | |
| | | $V_O = 4$ V _{PP} | $V_{CC} = \pm 5$ | | 93 | | |
| | | | $V_{CC} = \pm 15$ | | 95 | | |
| Third intermodulation distortion | | $V_{I(PP)} = 4$ V, G = 1, F1 = 3 MHz, F2 = 3.5 MHz | | | -53 | | dBc |
| Third-order intercept | | $V_{I(PP)} = 4$ V, G = 1, F1 = 3 MHz, F2 = 3.5 MHz | | | 41.5 | | dB |
| NOISE PERFORMANCE | | | | | | | |
| V_n | Input voltage noise | f = 10 kHz | | | 1.3 | | nV/ $\sqrt{\text{Hz}}$ |
| I_n | Input current noise | f = 10 kHz | | | 1 | | pA/ $\sqrt{\text{Hz}}$ |
| DC PERFORMANCE | | | | | | | |
| Open-loop gain | | $T_A = +25^\circ\text{C}$ | | 71 | 78 | | dB |
| | | $T_A = \text{full range}$ | | 69 | | | |
| $V_{(OS)}$ | Input offset voltage | $T_A = +25^\circ\text{C}$ | | | 0.2 | 2 | mV |
| | | $T_A = \text{full range}$ | | | | 3 | |
| | Common-mode input offset voltage, referred to V_{OCM} | | $T_A = +25^\circ\text{C}$ | | 0.2 | 3.5 | |
| | Input offset voltage drift | | $T_A = \text{full range}$ | | 4.5 | | |
| I_{IB} | Input bias current | $T_A = \text{full range}$ | | | 2 | 6 | μA |
| I_{OS} | Input offset current | $T_A = \text{full range}$ | | | 100 | 500 | nA |
| Offset drift | | $T_A = \text{full range}$ | | | 2 | | nA/ $^\circ\text{C}$ |

(1) The full range temperature is 0°C to $+70^\circ\text{C}$ for the C-suffix, and -40°C to $+85^\circ\text{C}$ for the I-suffix.

(2) Slew rate is measured from an output level range of 25% to 75%.

ELECTRICAL CHARACTERISTICS⁽¹⁾ (continued)

$V_{CC} = \pm 5\text{ V}$, $R_L = 800\Omega$, and $T_A = +25^\circ\text{C}$, unless otherwise noted.

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|--|---------------------------|------------|------------|------------|
| INPUT CHARACTERISTICS | | | | | | |
| CMRR | Common-mode rejection ratio | $T_A = \text{full range}$ | 80 | 95 | | dB |
| V_{ICR} | Common-mode input voltage range | | -3.77 to 4.3 | -4 to 4.5 | | V |
| R_I | Input resistance | Measured into each input terminal | | 34 | | M Ω |
| C_I | Input capacitance, closed loop | | | 4 | | pF |
| r_o | Output resistance | Open loop | | 41 | | Ω |
| OUTPUT CHARACTERISTICS | | | | | | |
| Output voltage swing | | $V_{CC} = 5\text{ V}$ | $T_A = +25^\circ\text{C}$ | 1.2 to 3.8 | 0.9 to 4.1 | V |
| | | | $T_A = \text{full range}$ | 1.3 to 3.7 | ± 4 | |
| | | $V_{CC} = \pm 5\text{ V}$ | $T_A = +25^\circ\text{C}$ | ± 3.7 | | |
| | | | $T_A = \text{full range}$ | ± 3.6 | | |
| I_O Output current | | $V_{CC} = 5\text{ V}, R_L = 7\ \Omega$ | $T_A = +25^\circ\text{C}$ | 25 | 45 | mA |
| | | | $T_A = \text{full range}$ | 20 | | |
| | | $V_{CC} = \pm 5\text{ V}, R_L = 7\ \Omega$ | $T_A = +25^\circ\text{C}$ | 30 | 55 | |
| | | | $T_A = \text{full range}$ | 28 | | |
| $V_{CC} = \pm 15\text{ V}, R_L = 7\ \Omega$ | $T_A = +25^\circ\text{C}$ | 60 | 85 | | | |
| | $T_A = \text{full range}$ | 65 | | | | |
| POWER SUPPLY | | | | | | |
| V_{CC} | Supply voltage range | Single supply | | 4 | 33 | V |
| | | Split supply | | ± 2 | ± 16.5 | |
| I_{CC} | Quiescent current | $V_{CC} = \pm 5\text{ V}$ | $T_A = +25^\circ\text{C}$ | 12.3 | 15 | mA |
| | | | $T_A = \text{full range}$ | | 16 | |
| $I_{CC(SD)}$ | Quiescent current (shutdown) (THS4130 only) ⁽³⁾ | $V = -5\text{ V}$ | $T_A = +25^\circ\text{C}$ | 0.86 | 1.4 | mA |
| | | | $T_A = \text{full range}$ | | 1.5 | |
| PSRR | Power-supply rejection ratio (dc) | | $T_A = +25^\circ\text{C}$ | 73 | 98 | dB |
| | | | $T_A = \text{full range}$ | 70 | | |

(3) For detailed information on the behavior of the power-down circuit, see the *Power-Down Mode* section in the *Principles of Operation*.

TYPICAL CHARACTERISTICS

TABLE OF GRAPHS

| | | FIGURE |
|------------|--|--|
| | Small-signal frequency response | Figure 1, Figure 2 |
| | Small-signal frequency response (various supplies) | Figure 3 |
| | Small-signal frequency response (various C_F) | Figure 4 |
| | Small-signal frequency response (various C_L) | Figure 5 |
| | Large-signal transient response (differential in/single out) | Figure 6 |
| | Large-signal frequency response | Figure 7 |
| CMMR | Common-mode rejection ratio | vs Frequency Figure 8 |
| I_{CC} | Supply current | vs Free-air temperature Figure 9 |
| | | vs Free-air temperature (shutdown state) Figure 10 |
| I_{IB} | Input bias current | vs Free-air temperature Figure 11 |
| | | Settling time Figure 12 |
| PSRR | Power-supply rejection ratio | vs Frequency (differential out) Figure 13 |
| | Large-signal transient response | Figure 14 |
| THD | Total harmonic distortion | vs Frequency Figure 15 |
| | Second-harmonic distortion | vs Frequency Figure 16, Figure 17 |
| | | vs Output voltage Figure 18, Figure 19 |
| | Third-harmonic distortion | vs Frequency Figure 20, Figure 21 |
| | | vs Output voltage Figure 22, Figure 23 |
| V_n | Voltage noise | vs Frequency Figure 24 |
| I_n | Current noise | vs Frequency Figure 25 |
| $V_{(OS)}$ | Input offset voltage | vs Common-mode output voltage Figure 26 |
| V_O | Output voltage | vs Differential load resistance Figure 27 |
| z_o | Output impedance | vs Frequency Figure 28 |

TYPICAL CHARACTERISTICS

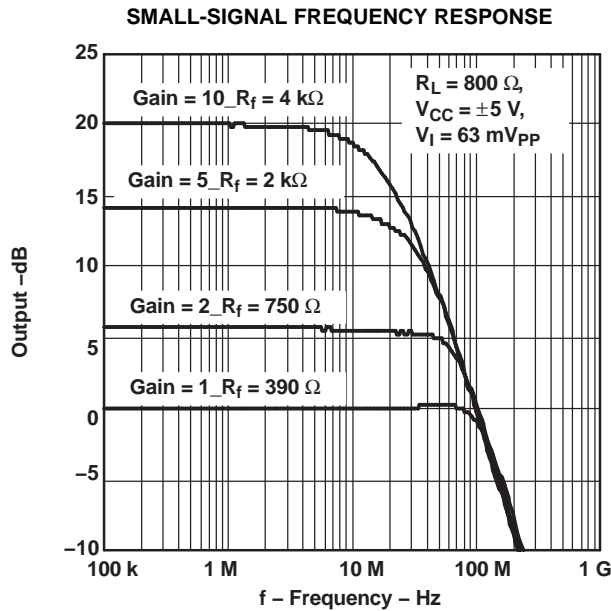


Figure 1.

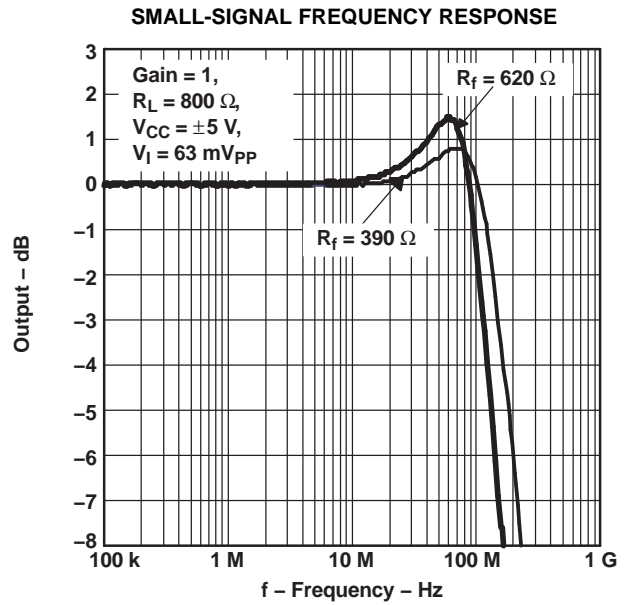


Figure 2.

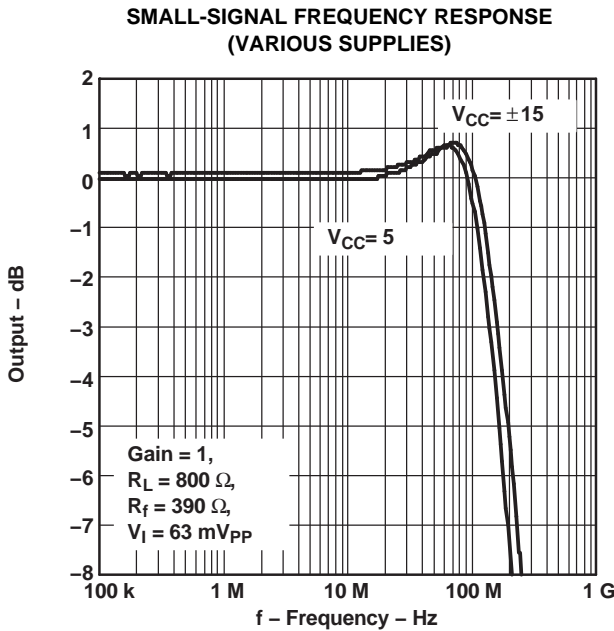


Figure 3.

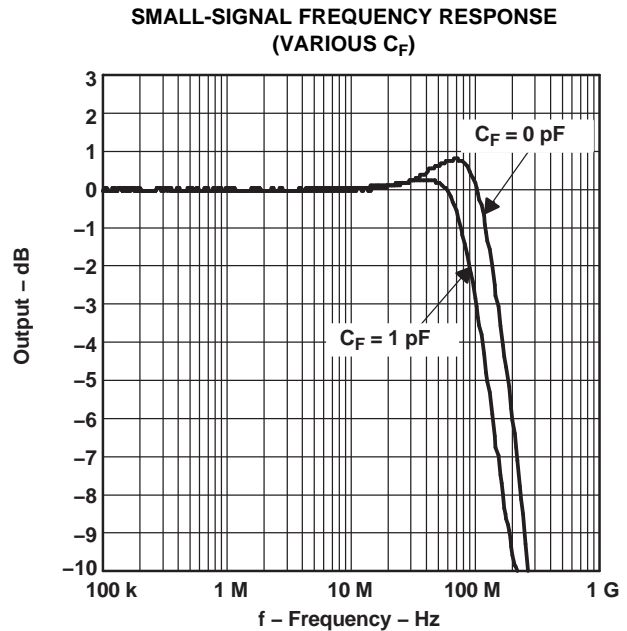


Figure 4.

TYPICAL CHARACTERISTICS (continued)

**SMALL-SIGNAL FREQUENCY RESPONSE
(VARIOUS C_L)**

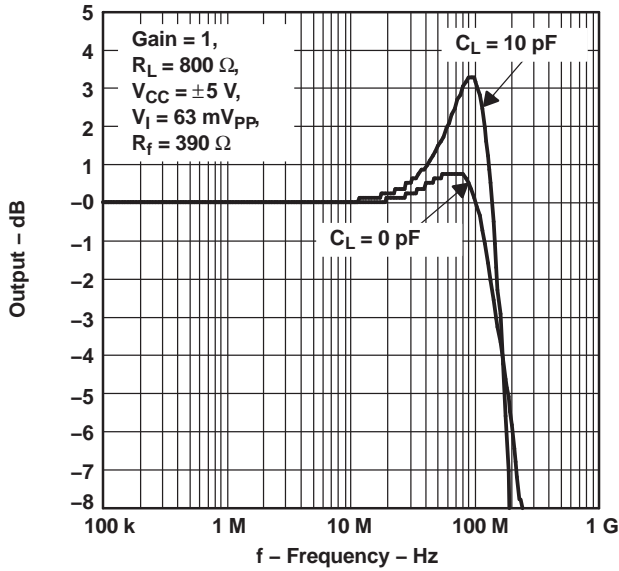


Figure 5.

**LARGE-SIGNAL TRANSIENT RESPONSE
(DIFFERENTIAL IN/SINGLE OUT)**

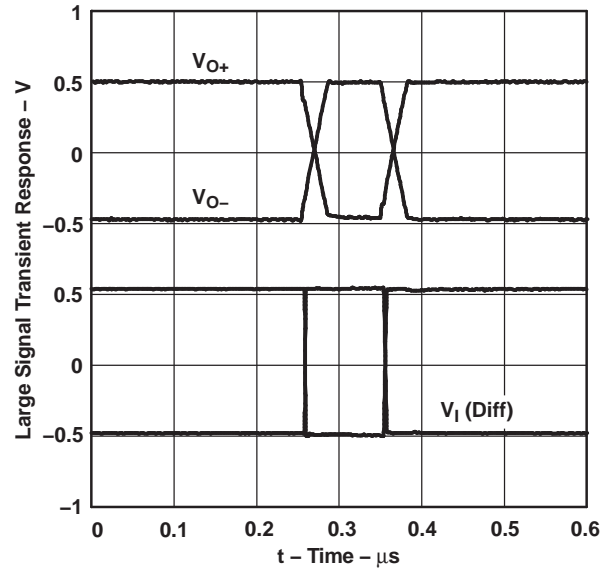


Figure 6.

LARGE-SIGNAL FREQUENCY RESPONSE

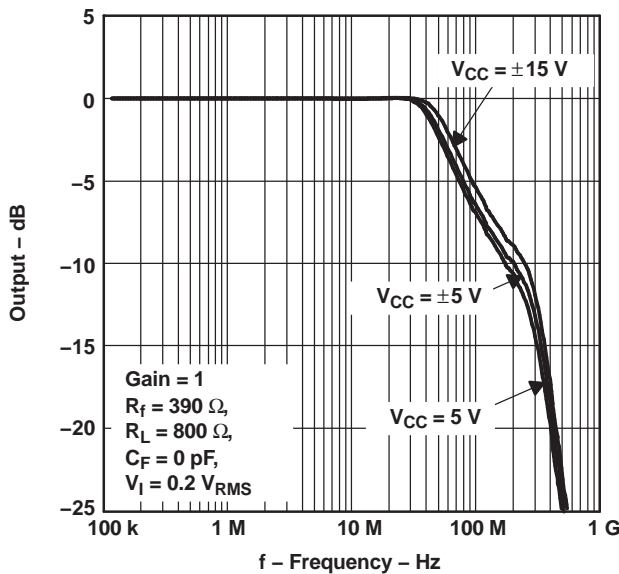


Figure 7.

**COMMON-MODE REJECTION RATIO
vs
FREQUENCY**

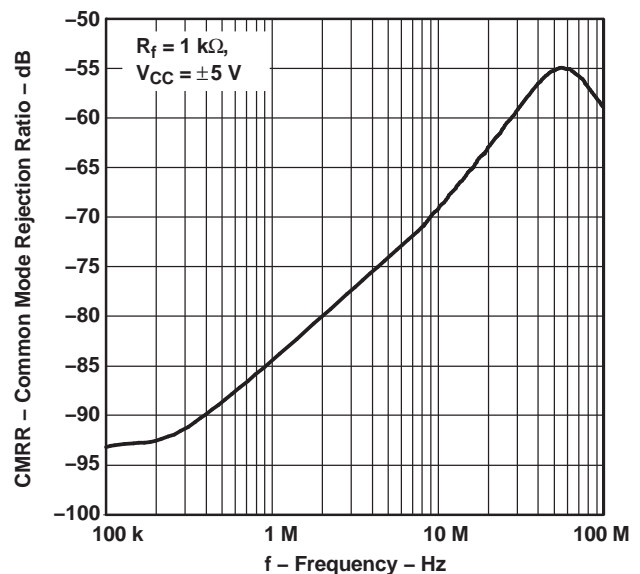
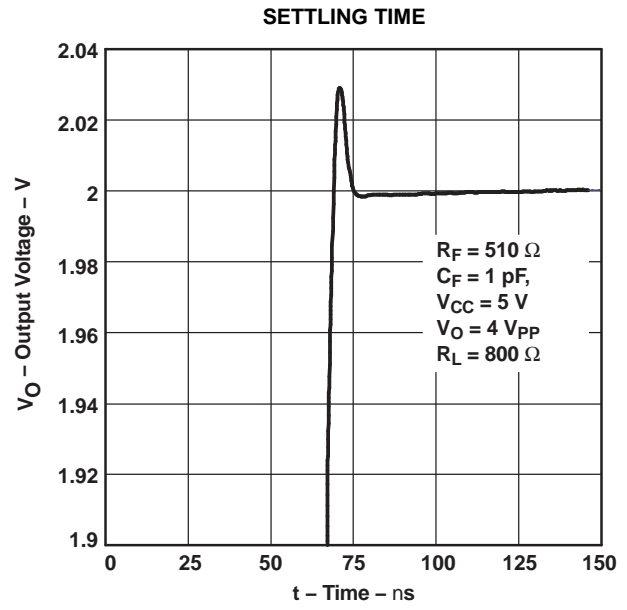
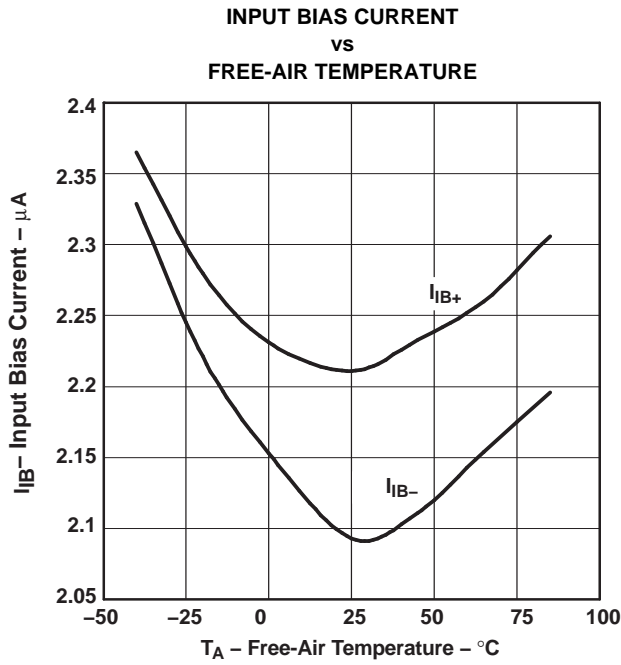
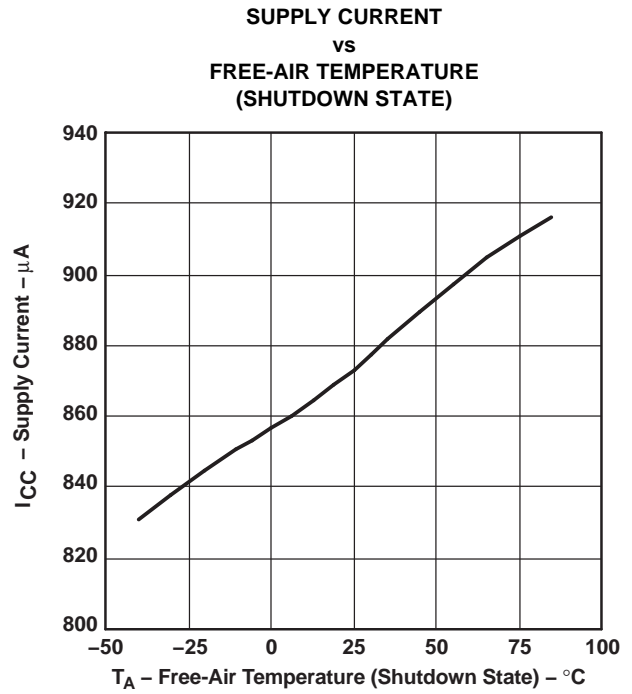
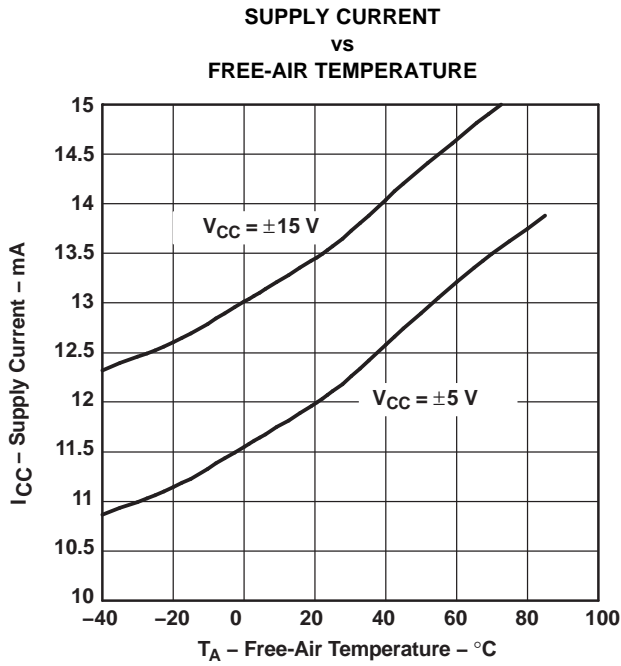


Figure 8.

TYPICAL CHARACTERISTICS (continued)



TYPICAL CHARACTERISTICS (continued)

POWER-SUPPLY REJECTION RATIO
vs
FREQUENCY (DIFFERENTIAL OUT)

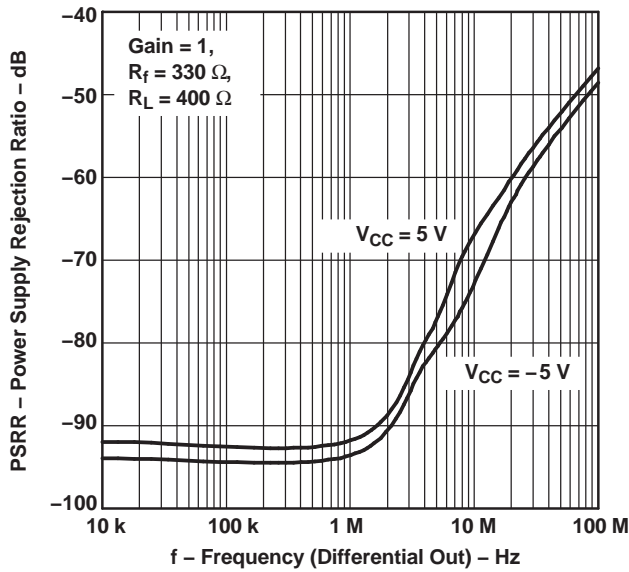


Figure 13.

LARGE-SIGNAL TRANSIENT RESPONSE

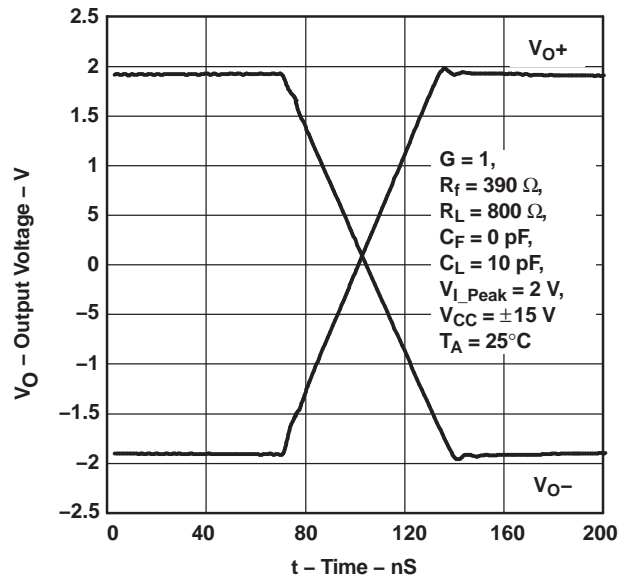


Figure 14.

TOTAL HARMONIC DISTORTION
vs
FREQUENCY

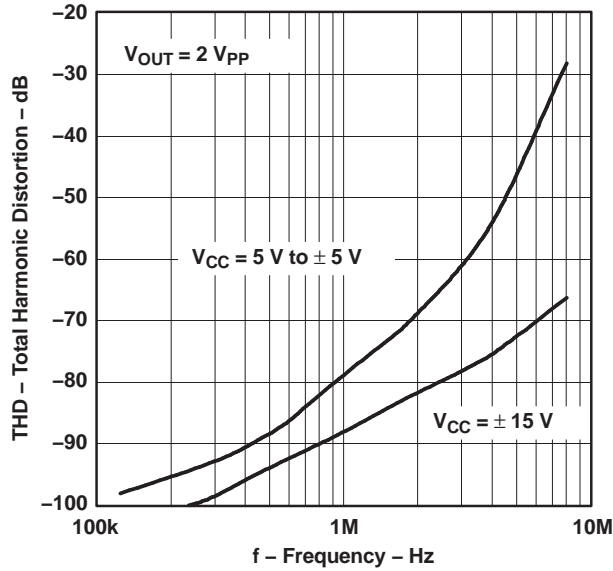


Figure 15.

SECOND-HARMONIC DISTORTION
vs
FREQUENCY

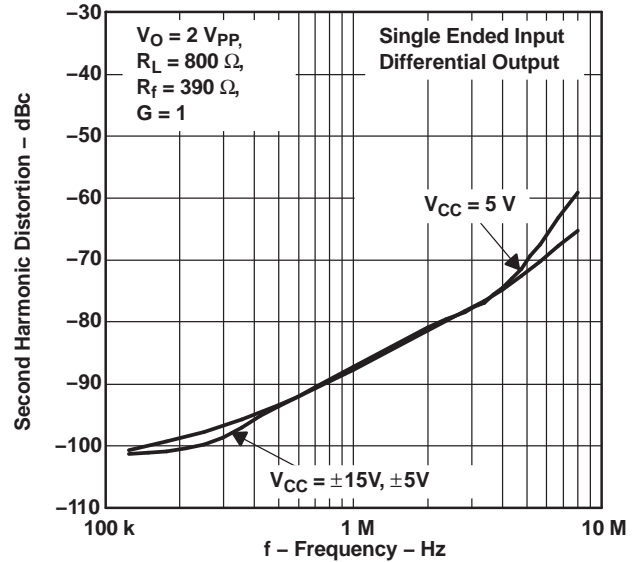


Figure 16.

TYPICAL CHARACTERISTICS (continued)

SECOND-HARMONIC DISTORTION
vs
FREQUENCY

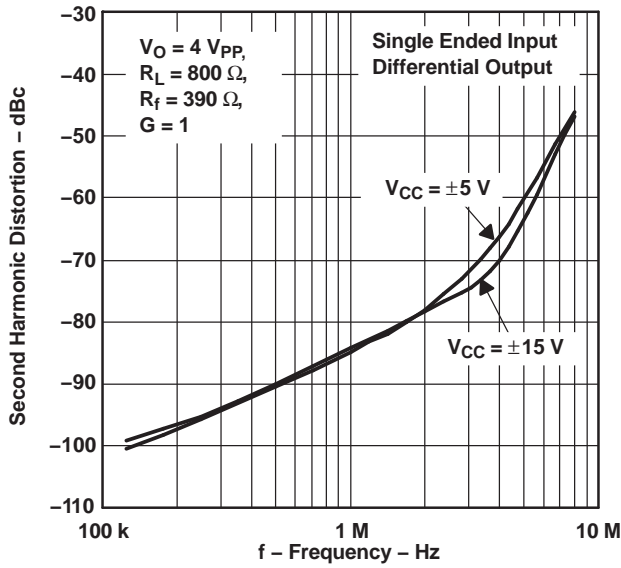


Figure 17.

SECOND-HARMONIC DISTORTION
vs
OUTPUT VOLTAGE

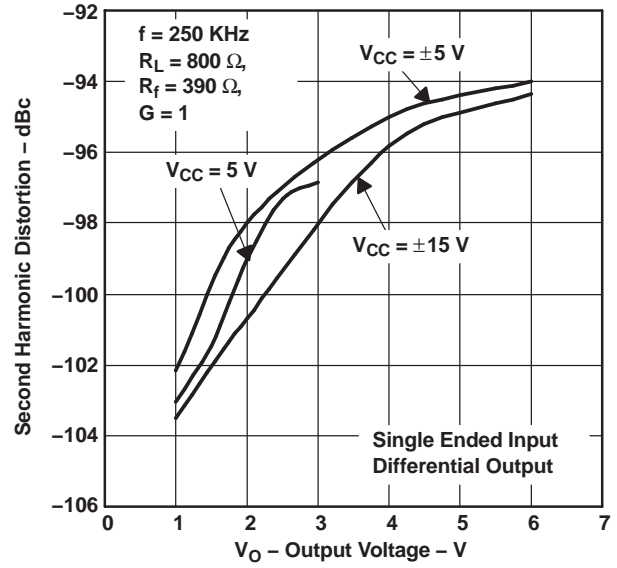


Figure 18.

SECOND-HARMONIC DISTORTION
vs
OUTPUT VOLTAGE

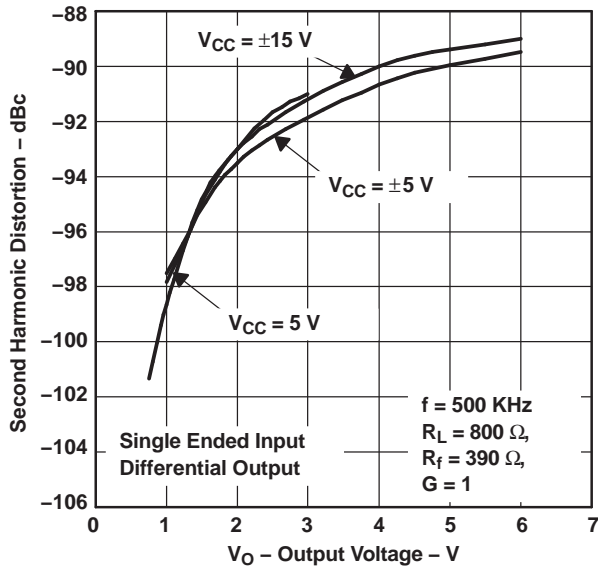


Figure 19.

THIRD-HARMONIC DISTORTION
vs
FREQUENCY

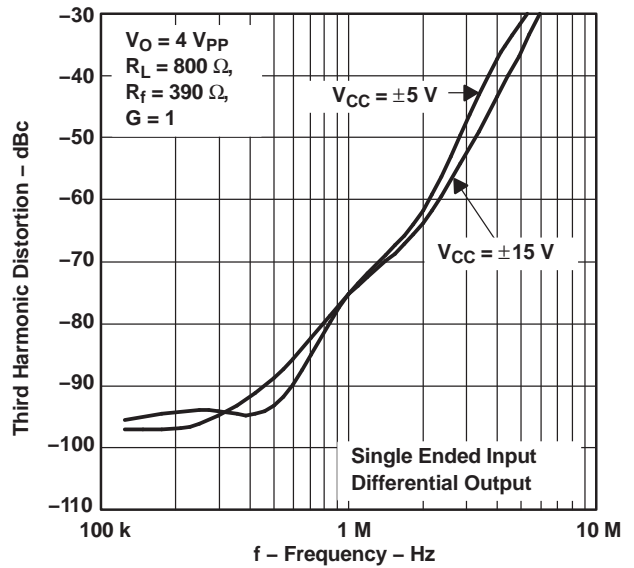


Figure 20.

TYPICAL CHARACTERISTICS (continued)

THIRD-HARMONIC DISTORTION
vs
FREQUENCY

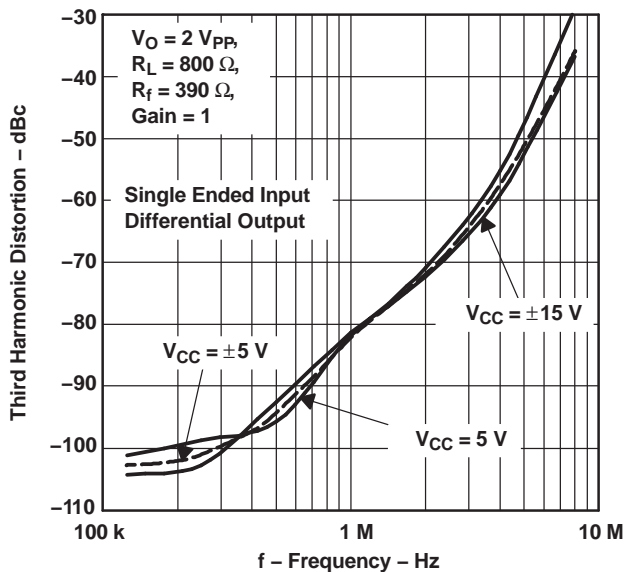


Figure 21.

THIRD-HARMONIC DISTORTION
vs
OUTPUT VOLTAGE

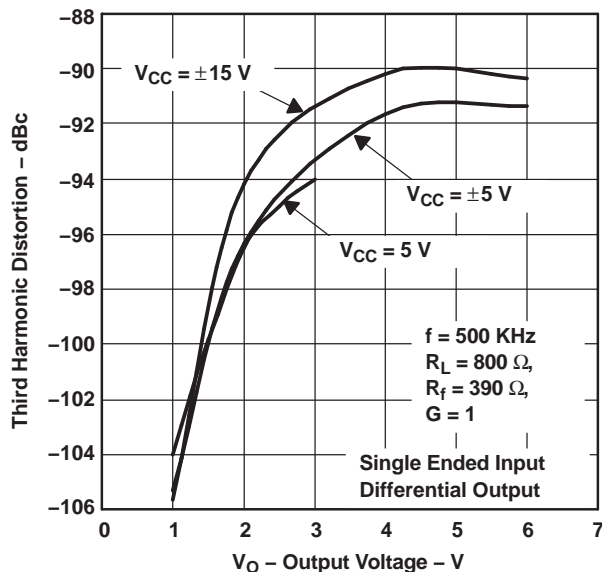


Figure 22.

THIRD-HARMONIC DISTORTION
vs
OUTPUT VOLTAGE

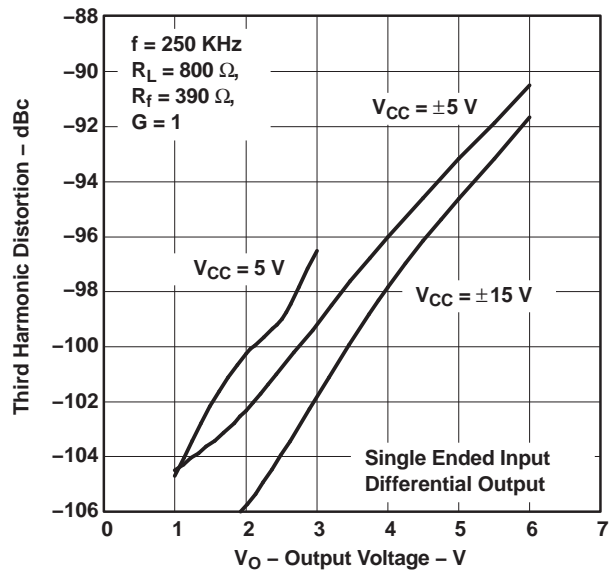


Figure 23.

VOLTAGE NOISE
vs
FREQUENCY

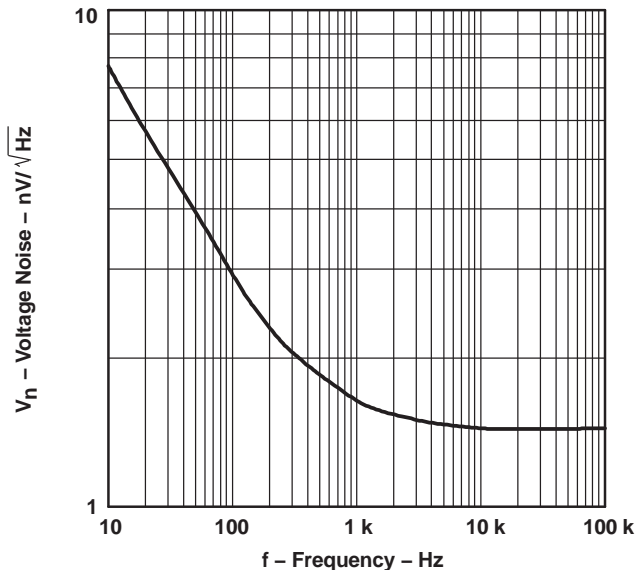


Figure 24.

TYPICAL CHARACTERISTICS (continued)

CURRENT NOISE
vs
FREQUENCY

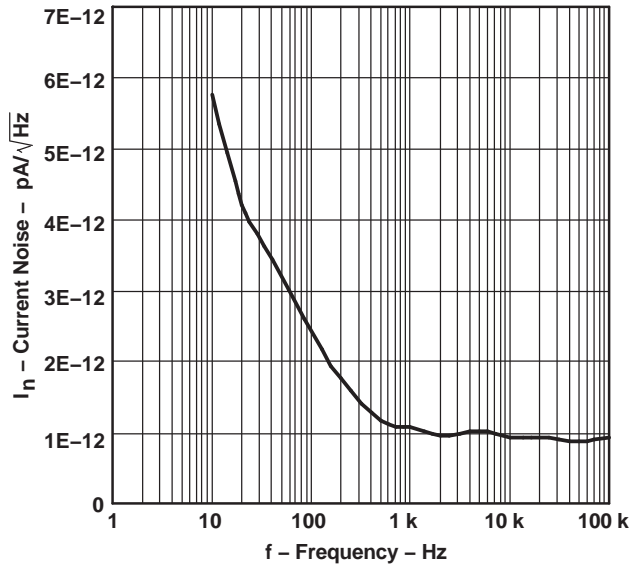


Figure 25.

INPUT OFFSET VOLTAGE
vs
COMMON-MODE OUTPUT VOLTAGE

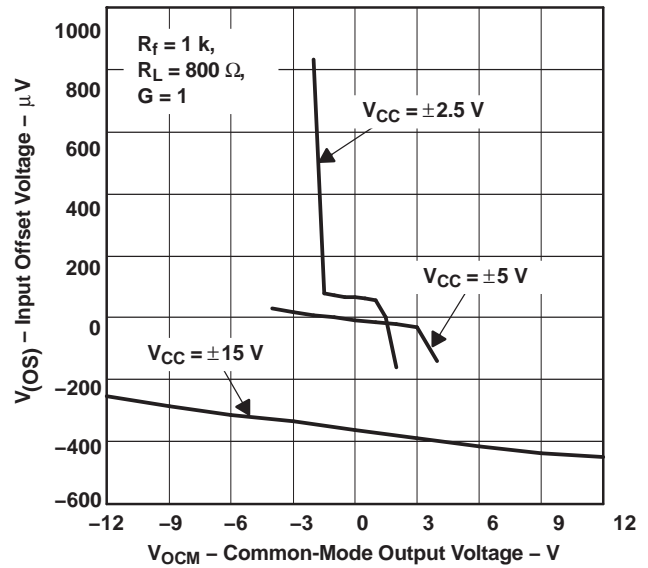


Figure 26.

OUTPUT VOLTAGE
vs
DIFFERENTIAL LOAD RESISTANCE

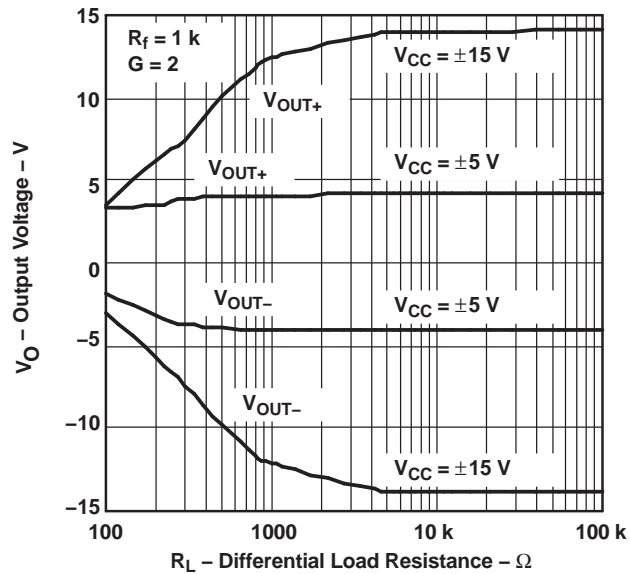


Figure 27.

OUTPUT IMPEDANCE
vs
FREQUENCY

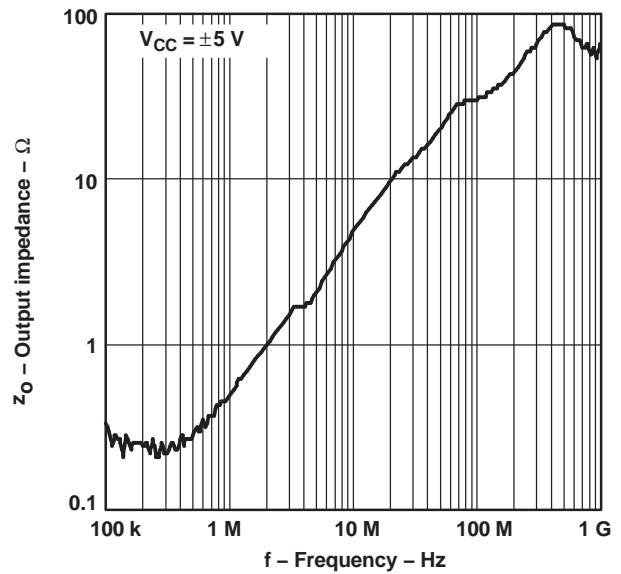


Figure 28.

APPLICATION INFORMATION

RESISTOR MATCHING

Resistor matching is important in fully-differential amplifiers. The balance of the output on the reference voltage depends on matched ratios of the resistor. CMRR, PSRR, and cancellation of the second-harmonic distortion diminish if resistor mismatch occurs. Therefore, it is recommended to use 1% tolerance resistors or better to keep the performance optimized.

V_{OCM} sets the dc level of the output signals. If no voltage is applied to the V_{OCM} pin, it is set to the midrail voltage internally defined as:

$$\frac{(V_{CC+}) + (V_{CC-})}{2} \tag{1}$$

In the differential mode, the V_{OCM} on the two outputs cancel each other. Therefore, the output in the differential mode is the same as the input in the gain of 1. V_{OCM} has a high bandwidth capability up to the typical operation range of the amplifier. For the prevention of noise going through the device, use a 0.1 μF capacitor on the V_{OCM} pin as a bypass capacitor. Figure 29 shows the simplified diagram of the THS413x.

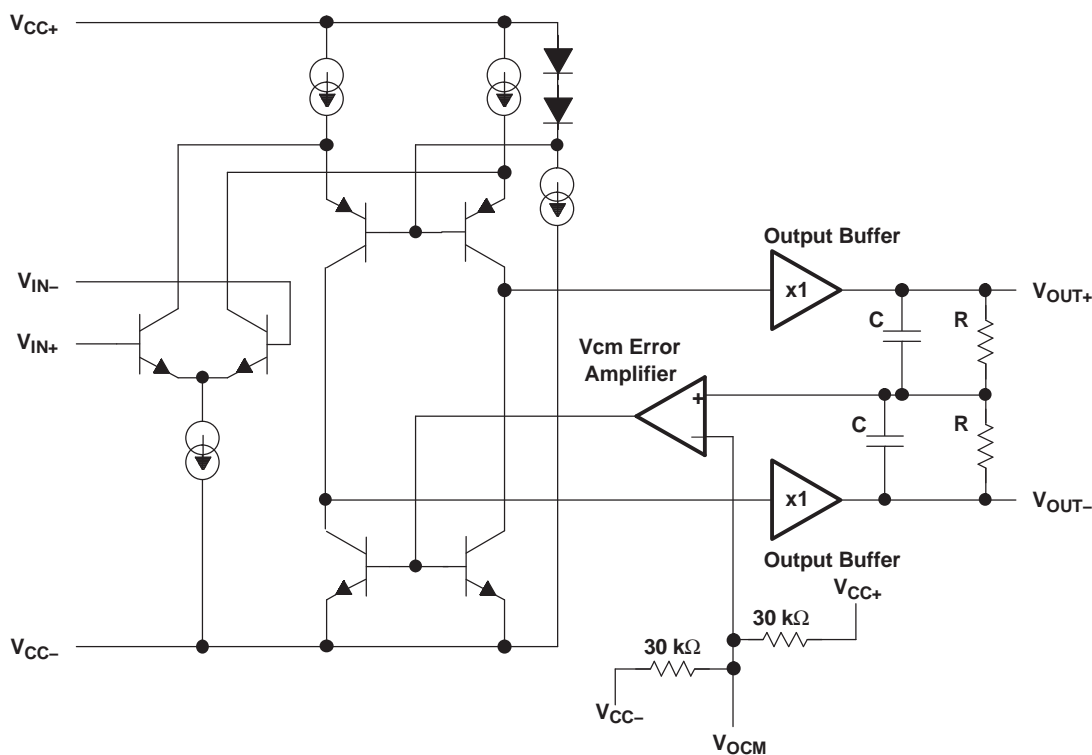


Figure 29. THS413x Simplified Diagram

DATA CONVERTERS

Data converters are one of the most popular applications for the fully-differential amplifiers. Figure 30 shows a typical configuration of a fully-differential amplifier attached to a differential analog-to-digital converter (ADC).

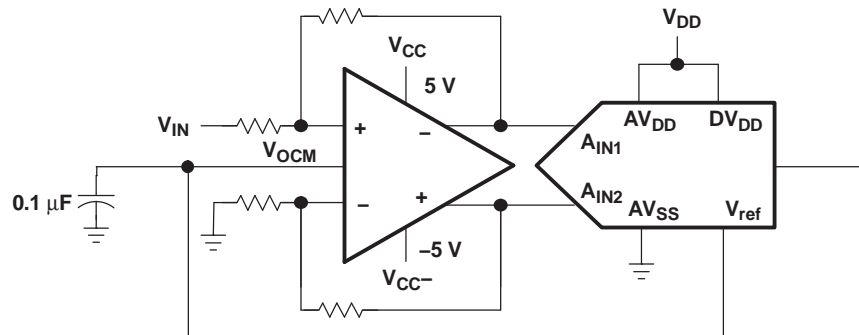


Figure 30. Fully-Differential Amplifier Attached to a Differential ADC

Fully-differential amplifiers can operate with a single supply. V_{OCM} defaults to the midrail voltage, $V_{CC}/2$. The differential output may be fed into a data converter. This method eliminates the use of a transformer in the circuit. If the ADC has a reference voltage output (V_{ref}), then it is recommended to connect it directly to the V_{OCM} of the amplifier using a bypass capacitor for stability. For proper operation, the input common-mode voltage to the input terminal of the amplifier should not exceed the common-mode input voltage range.

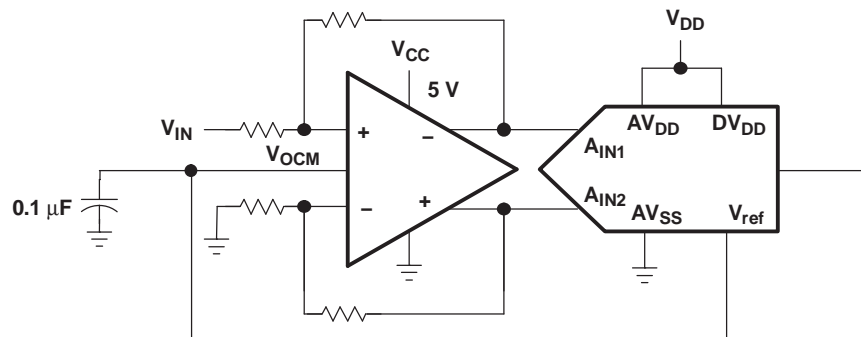


Figure 31. Fully-Differential Amplifier Using a Single Supply

Some single-supply applications may require the input voltage to exceed the common-mode input voltage range. In such cases, the circuit configuration of Figure 32 is suggested to bring the common-mode input voltage within the specifications of the amplifier.

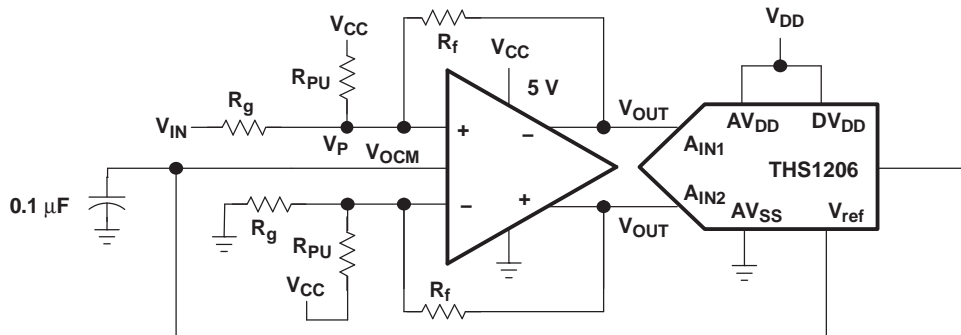


Figure 32. Circuit With Improved Common-Mode Input Voltage

Equation 2 is used to calculate R_{PU} :

$$R_{PU} = \frac{V_P - V_{CC}}{\left((V_{IN} - V_P) \frac{1}{R_G} + (V_{OUT} - V_P) \frac{1}{R_F} \right)} \quad (2)$$

DRIVING A CAPACITIVE LOAD

Driving capacitive loads with high-performance amplifiers is not a problem as long as certain precautions are taken. The first is to realize that the THS413x has been internally compensated to maximize its bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output decreases the device phase margin leading to high-frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series with the output of the amplifier, as shown in Figure 33. A minimum value of 20 Ω should work well for most applications. For example, in 50-Ω transmission systems, setting the series resistor value to 50 Ω both isolates any capacitance loading and provides the proper line impedance matching at the source end.

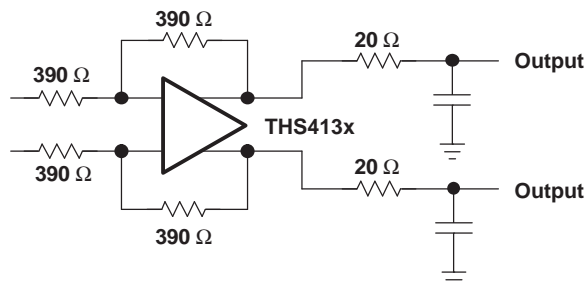


Figure 33. Driving a Capacitive Load

ACTIVE ANTIALIAS FILTERING

For signal conditioning in ADC applications, it is important to limit the input frequency to the ADC. Low-pass filters can prevent the aliasing of the high-frequency noise with the frequency of operation. Figure 34 presents a method by which the noise may be filtered in the THS413x.

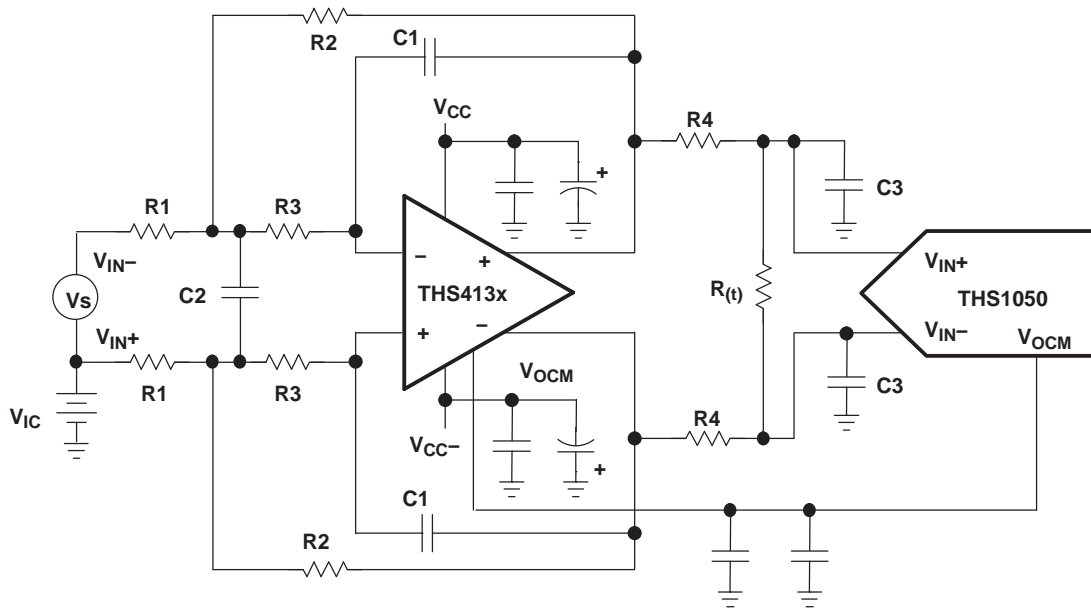


Figure 34. Antialias Filtering

The transfer function for this filter circuit is:

$$H_d(f) = \left[\frac{K}{-\left(\frac{f}{\text{FSF} \times f_c}\right)^2 + \frac{1}{Q} \frac{jf}{\text{FSF} \times f_c} + 1} \right] \times \left[\frac{\frac{R_t}{2R_4 + R_t}}{1 + \frac{j2\pi f R_4 R_t C_3}{2R_4 + R_t}} \right] \quad \text{Where } K = \frac{R_2}{R_1} \quad (3)$$

$$\text{FSF} \times f_c = \frac{1}{2\pi \sqrt{2 \times R_2 R_3 C_1 C_2}} \quad \text{and } Q = \frac{\sqrt{2 \times R_2 R_3 C_1 C_2}}{R_3 C_1 + R_2 C_1 + K R_3 C_1} \quad (4)$$

K sets the pass band gain, f_c is the cutoff frequency for the filter, FSF is a frequency scaling factor, and Q is the quality factor.

$$\text{FSF} = \sqrt{\text{Re}^2 + |\text{Im}|^2} \quad \text{and } Q = \frac{\sqrt{\text{Re}^2 + |\text{Im}|^2}}{2\text{Re}} \quad (5)$$

where Re is the real part, and Im is the imaginary part of the complex pole pair. Setting $R_2 = R$, $R_3 = mR$, $C_1 = C$, and $C_2 = nC$ results in:

$$\text{FSF} \times f_c = \frac{1}{2\pi R C \sqrt{2 \times mn}} \quad \text{and } Q = \frac{\sqrt{2 \times mn}}{1 + m(1 + K)} \quad (6)$$

Start by determining the ratios, m and n, required for the gain and Q of the filter type being designed, then select C and calculate R for the desired f_c .

PRINCIPLES OF OPERATION

THEORY OF OPERATION

The THS413x is a fully-differential amplifier. Differential amplifiers are typically *differential in/single out*, whereas fully-differential amplifiers are *differential in/differential out*.

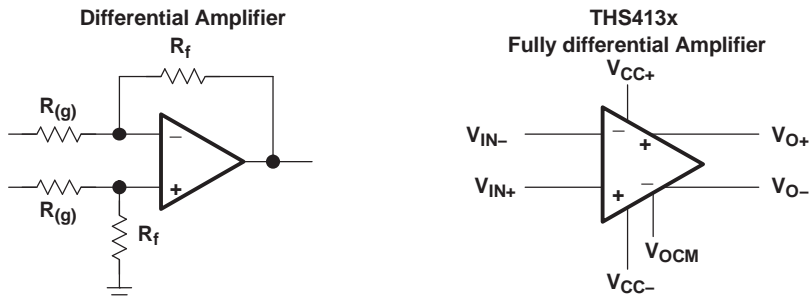


Figure 35. Differential Amplifier Versus a Fully-Differential Amplifier

To understand the THS413x fully-differential amplifiers, the definition for the pin outs of the amplifier are provided.

$$\text{Input voltage definition} \quad V_{ID} = (V_{I+}) - (V_{I-}) \quad V_{IC} = \frac{(V_{I+}) + (V_{I-})}{2} \quad (7)$$

$$\text{Output voltage definition} \quad V_{OD} = (V_{O+}) - (V_{O-}) \quad V_{OC} = \frac{(V_{O+}) + (V_{O-})}{2} \quad (8)$$

$$\text{Transfer function} \quad V_{OD} = V_{ID} \times A_{(f)} \quad (9)$$

$$\text{Output common mode voltage} \quad V_{OC} = V_{OCM} \quad (10)$$

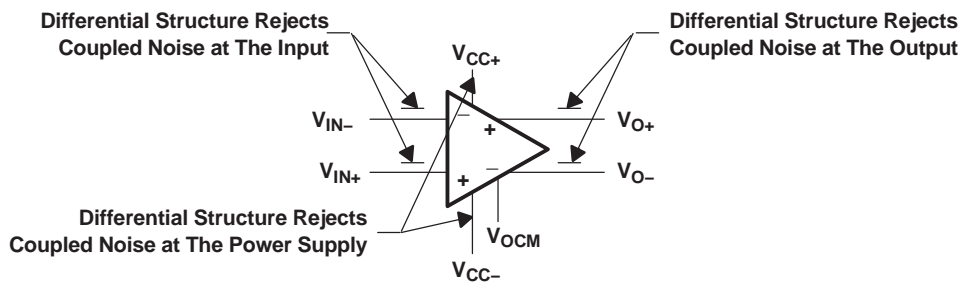
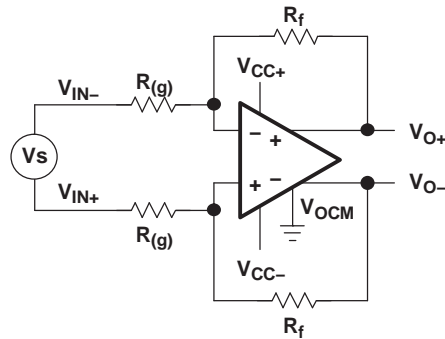


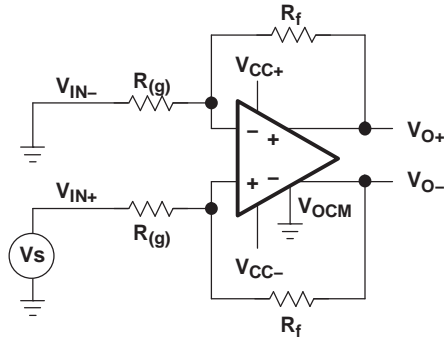
Figure 36. Definition of the Fully-Differential Amplifier

Figure 37 and Figure 38 depict the differences between the operation of the THS413x fully-differential amplifier in two different modes. Fully-differential amplifiers can work with differential input or can be implemented as single in/differential out.



Note: For proper operation, maintain symmetry by setting $R_{f1} = R_{f2} = R_f$ and $R_{(g)1} = R_{(g)2} = R_{(g)} \Rightarrow A = R_f/R_{(g)}$

Figure 37. Amplifying Differential Signals



RECOMMENDED RESISTOR VALUES

| GAIN | $R_{(g)}$ Ω | R_f Ω |
|------|--------------------|----------------|
| 1 | 390 | 390 |
| 2 | 374 | 750 |
| 5 | 402 | 2010 |
| 10 | 402 | 4020 |

Figure 38. Single In With Differential Out

If each output is measured independently, each output is one-half of the input signal when gain is 1. The following equations express the transfer function for each output:

$$V_O = \frac{1}{2} V_I \tag{11}$$

The second output is equal and opposite in sign:

$$V_O = -\frac{1}{2} V_I \tag{12}$$

Fully-differential amplifiers may be viewed as two inverting amplifiers. In this case, the equation of an inverting amplifier holds true for gain calculations. One advantage of fully-differential amplifiers is that they offer twice as much dynamic range compared to single-ended amplifiers. For example, a 1- V_{PP} ADC can only support an input signal of 1 V_{PP} . If the output of the amplifier is 2 V_{PP} , then it is not as practical to feed a 2- V_{PP} signal into the targeted ADC. Using a fully-differential amplifier enables the user to break down the output into two 1- V_{PP} signals with opposite signs and feed them into the differential input nodes of the ADC. In practice, the designer has been able to feed a 2-V peak-to-peak signal into a 1-V differential ADC with the help of a fully-differential amplifier. The final result indicates twice as much dynamic range. Figure 39 illustrates the increase in dynamic range. The gain factor should be considered in this scenario. The THS413x fully-differential amplifier offers an improved CMRR and PSRR due to its symmetrical input and output. Furthermore, second-harmonic distortion is improved. Second harmonics tend to cancel because of the symmetrical output.

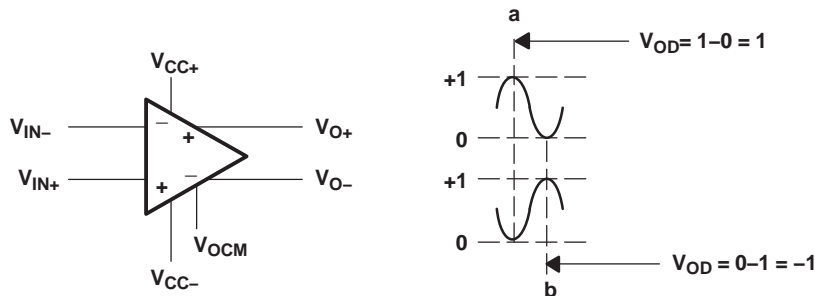


Figure 39. Fully-Differential Amplifier With Two 1- V_{PP} Signals

Similar to the standard inverting amplifier configuration, input impedance of a fully-differential amplifier is selected by the input resistor, $R_{(g)}$. If input impedance is a constraint in design, the designer may choose to implement the differential amplifier as an instrumentation amplifier. This configuration improves the input impedance of the fully-differential amplifier. Figure 40 depicts the general format of instrumentation amplifiers.

The general transfer function for this circuit is:

$$\frac{V_{OD}}{V_{IN1} - V_{IN2}} = \frac{R_f}{R_{(g)}} \left(1 + \frac{2R_2}{R_1} \right) \tag{13}$$

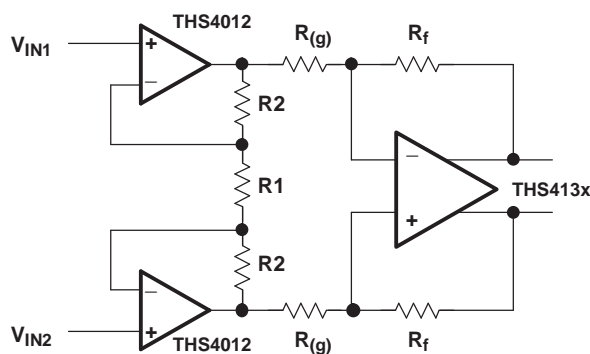


Figure 40. Instrumentation Amplifier

CIRCUIT LAYOUT CONSIDERATIONS

To achieve the levels of high-frequency performance of the THS413x, follow proper printed-circuit board (PCB) high-frequency design techniques. A general set of guidelines is given below. In addition, a THS413x evaluation board is available to use as a guide for layout or for evaluating the device performance.

- **Ground planes**—It is highly recommended that a ground plane be used on the board to provide all components with a low inductive ground connection. However, in the areas of the amplifier inputs and output, the ground plane can be removed to minimize the stray capacitance.
- **Proper power-supply decoupling**—Use a 6.8- μ F tantalum capacitor in parallel with a 0.1- μ F ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1- μ F ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1- μ F capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- **Sockets**—Sockets are not recommended for high-speed operational amplifiers. The additional lead inductance in the socket pins often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board are the best implementation.
- **Short trace runs/compact part placements**—Optimum high-frequency performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible, thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This helps to minimize stray capacitance at the input of the amplifier.
- **Surface-mount passive components**—Using surface-mount passive components is recommended for high-frequency amplifier circuits for several reasons. First, because of the extremely low lead inductance of surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be kept as short as possible.

POWER-DOWN MODE

The power-down mode is used when power saving is required. The power-down terminal ($\overline{\text{PD}}$) found on the THS413x is an active low terminal. If it is left as a no-connect terminal, the device always stays on due to an internal 50 k Ω resistor to V_{CC} . The threshold voltage for this terminal is approximately 1.4 V above $V_{\text{CC-}}$. This means that if the $\overline{\text{PD}}$ terminal is 1.4 V above $V_{\text{CC-}}$, the device is active. If the $\overline{\text{PD}}$ terminal is less than 1.4 V above $V_{\text{CC-}}$, the device is off. For example, if $V_{\text{CC-}} = -5$ V, then the device is on when $\overline{\text{PD}}$ reaches -3.6 V, (-5 V + 1.4 V = -3.6 V). By the same calculation, the device is off below -3.6 V. It is recommended to pull the terminal to $V_{\text{CC-}}$ in order to turn the device off. Figure 41 shows the simplified version of the power-down circuit. While in the power-down state, the amplifier goes into a high-impedance state. The amplifier output impedance is typically greater than 1 M Ω in the power-down state.

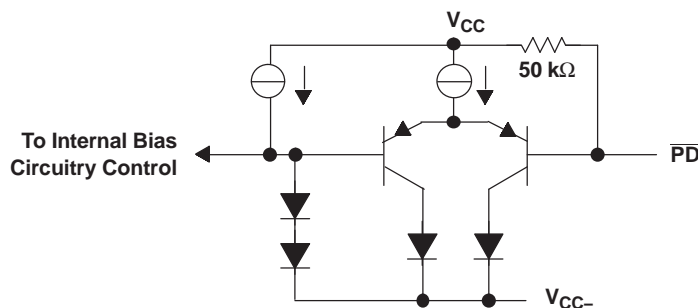


Figure 41. Simplified Power-Down Circuit

Due to the similarity of the standard inverting amplifier configuration, the output impedance appears to be very low while in the power-down state. This is because the feedback resistor (R_f) and the gain resistor ($R_{(g)}$) are still connected to the circuit. Therefore, a current path is allowed between the input of the amplifier and the output of the amplifier. An example of the closed loop output impedance is shown in Figure 42.

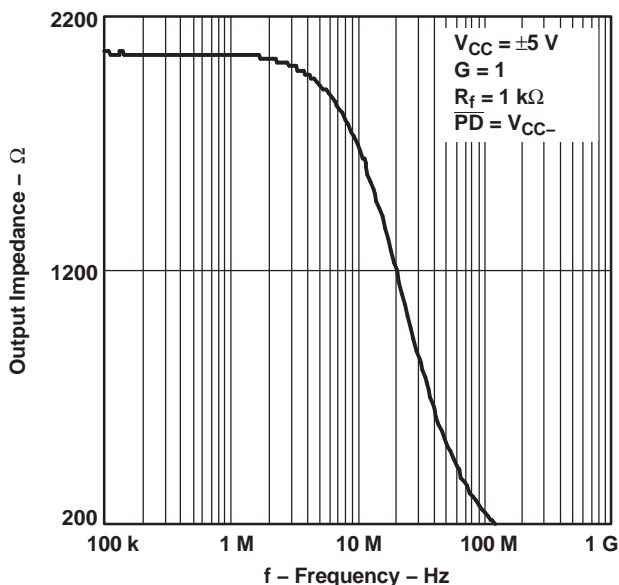


Figure 42. Output Impedance (In Power-Down) vs Frequency

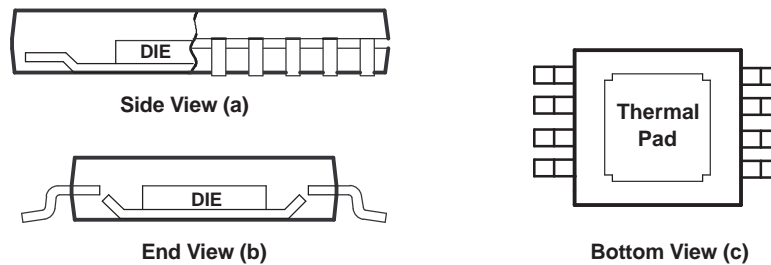
GENERAL PowerPAD DESIGN CONSIDERATIONS

The THS413x is available packaged in a thermally-enhanced DGN package, which is a member of the PowerPAD family of packages. This package is constructed using a downset leadframe upon which the die is mounted (see [Figure 43a](#) and [Figure 43b](#)). This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package (see [Figure 43c](#)). Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of the surface mount with the previously awkward mechanical methods of heatsinking.

More complete details of the PowerPAD installation process and thermal management techniques can be found in the Texas Instruments Technical Brief, ([PowerPAD Thermally-Enhanced Package SLMA002](#)). This document can be found at the TI web site (www.ti.com) by searching on the key word PowerPAD. The document can also be ordered through your local TI sales office. Refer to literature number SLMA002 when ordering.



- A. The thermal pad (PowerPAD) is electrically isolated from all other pins and can be connected to any potential from V_{CC-} to V_{CC+} . Typically, the thermal pad is connected to the ground plane because this plane tends to physically be the largest and is able to dissipate the most amount of heat.

Figure 43. Views of Thermally-Enhanced DGN Package

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision G (January 2010) to Revision H Page

- Changed footnote A in [Figure 43](#) 22
-

Changes from Revision F (January 2006) to Revision G Page

- Changed DGK package specifications in the *Dissipation Rating* table 2
-

PACKAGING INFORMATION

| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|-----------------------|-------------------|-----------------|------|-------------|----------------------------|----------------------|------------------------------|-----------------------------|
| THS4130CD | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGK | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGKG4 | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGKR | ACTIVE | VSSOP | DGK | 8 | | TBD | Call TI | Call TI | |
| THS4130CDGKRG4 | ACTIVE | VSSOP | DGK | 8 | | TBD | Call TI | Call TI | |
| THS4130CDGN | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGNG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGNR | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130CDGNRG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130ID | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGK | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGKG4 | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGKR | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGKRG4 | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGN | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGNG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |

| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|-----------------------|-------------------|-----------------|------|-------------|----------------------------|----------------------|------------------------------|-----------------------------|
| THS4130IDGNR | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDGNRG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4130IDRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CD | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGK | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGKG4 | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGKR | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGKRG4 | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGN | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGNG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGNR | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDGNRG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131CDRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131ID | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |

| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|-----------------------|-------------------|-----------------|------|-------------|-------------------------|----------------------|------------------------------|-----------------------------|
| THS4131IDGK | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGKG4 | ACTIVE | VSSOP | DGK | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGKR | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGKRG4 | ACTIVE | VSSOP | DGK | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGN | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGNG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 80 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGNR | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDGNRG4 | ACTIVE | MSOP- PowerPAD | DGN | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| THS4131IDRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


| | |
|----|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

TAPE AND REEL INFORMATION

*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|----------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| THS4130CDGNR | MSOP-Power PAD | DGN | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4130IDGKR | VSSOP | DGK | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4130IDGNR | MSOP-Power PAD | DGN | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4130IDR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| THS4131CDGKR | VSSOP | DGK | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4131CDGNR | MSOP-Power PAD | DGN | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4131CDR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| THS4131IDGKR | VSSOP | DGK | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4131IDGNR | MSOP-Power PAD | DGN | 8 | 2500 | 330.0 | 12.4 | 5.3 | 3.4 | 1.4 | 8.0 | 12.0 | Q1 |
| THS4131IDR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

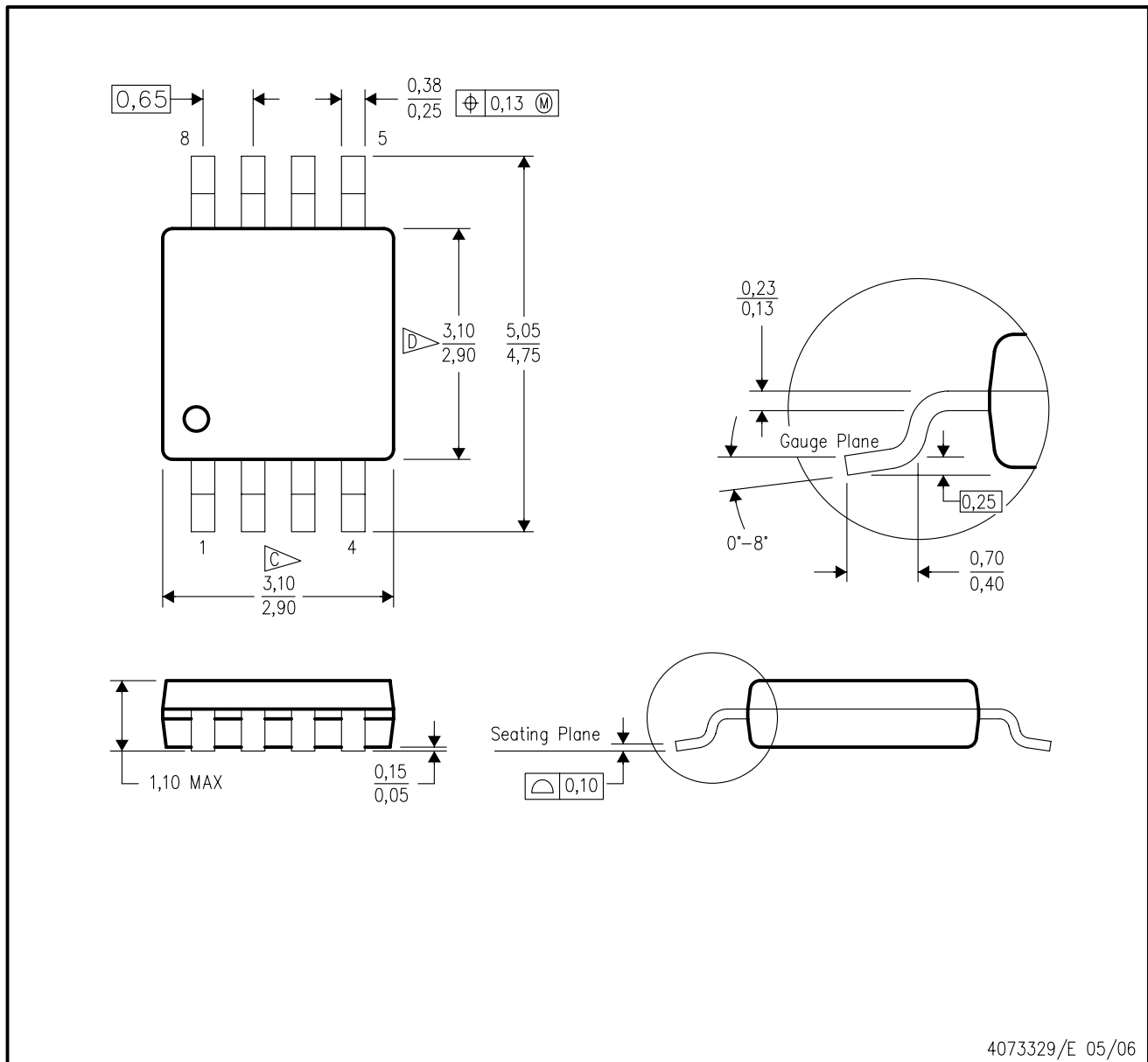
TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|---------------|-----------------|------|------|-------------|------------|-------------|
| THS4130CDGNR | MSOP-PowerPAD | DGN | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4130IDGKR | VSSOP | DGK | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4130IDGNR | MSOP-PowerPAD | DGN | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4130IDR | SOIC | D | 8 | 2500 | 367.0 | 367.0 | 35.0 |
| THS4131CDGKR | VSSOP | DGK | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4131CDGNR | MSOP-PowerPAD | DGN | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4131CDR | SOIC | D | 8 | 2500 | 367.0 | 367.0 | 35.0 |
| THS4131IDGKR | VSSOP | DGK | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4131IDGNR | MSOP-PowerPAD | DGN | 8 | 2500 | 358.0 | 335.0 | 35.0 |
| THS4131IDR | SOIC | D | 8 | 2500 | 367.0 | 367.0 | 35.0 |

DGK (S-PDSO-G8)

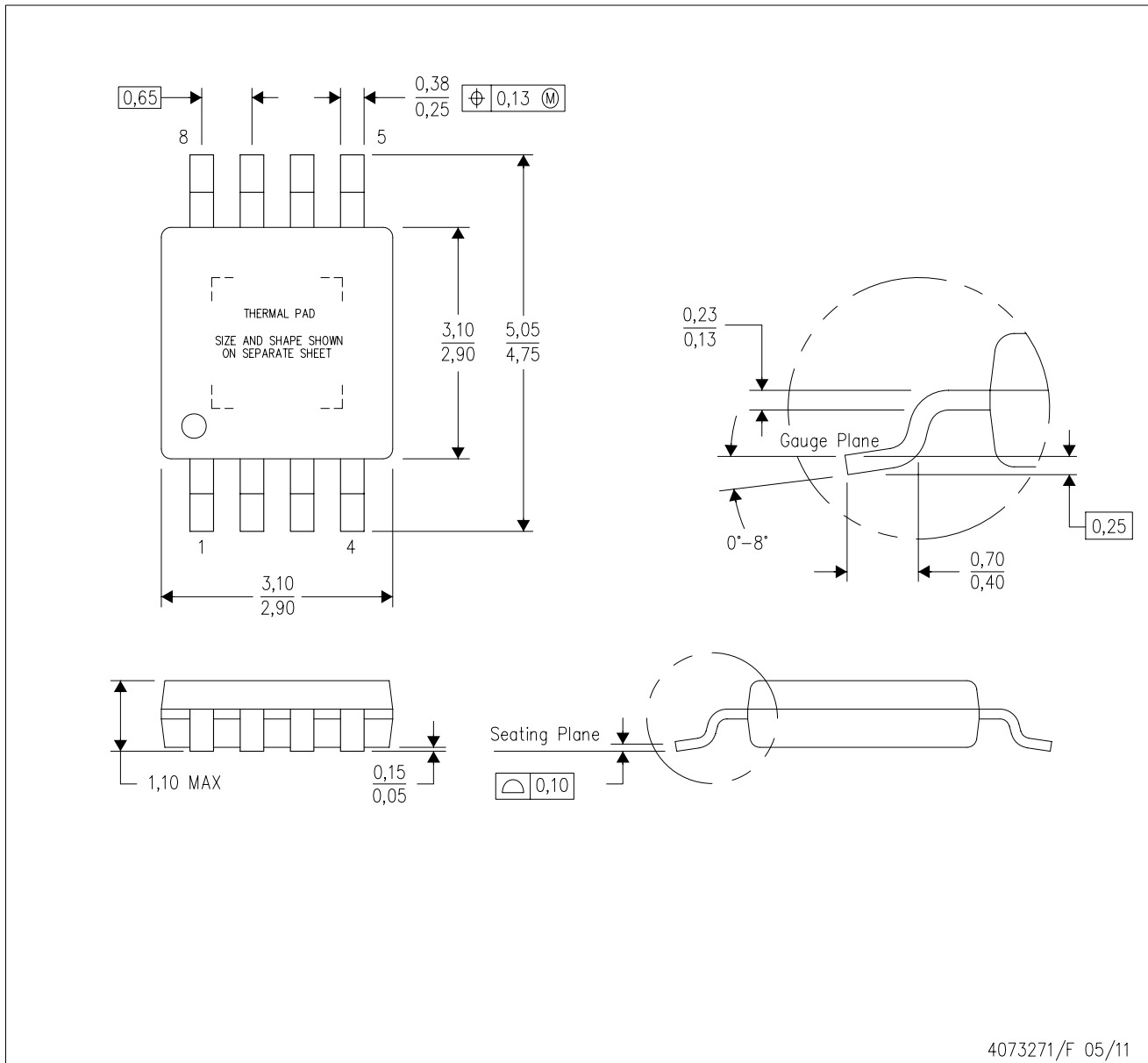
PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
 - E. Falls within JEDEC MO-187 variation AA, except interlead flash.

DGN (S-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE

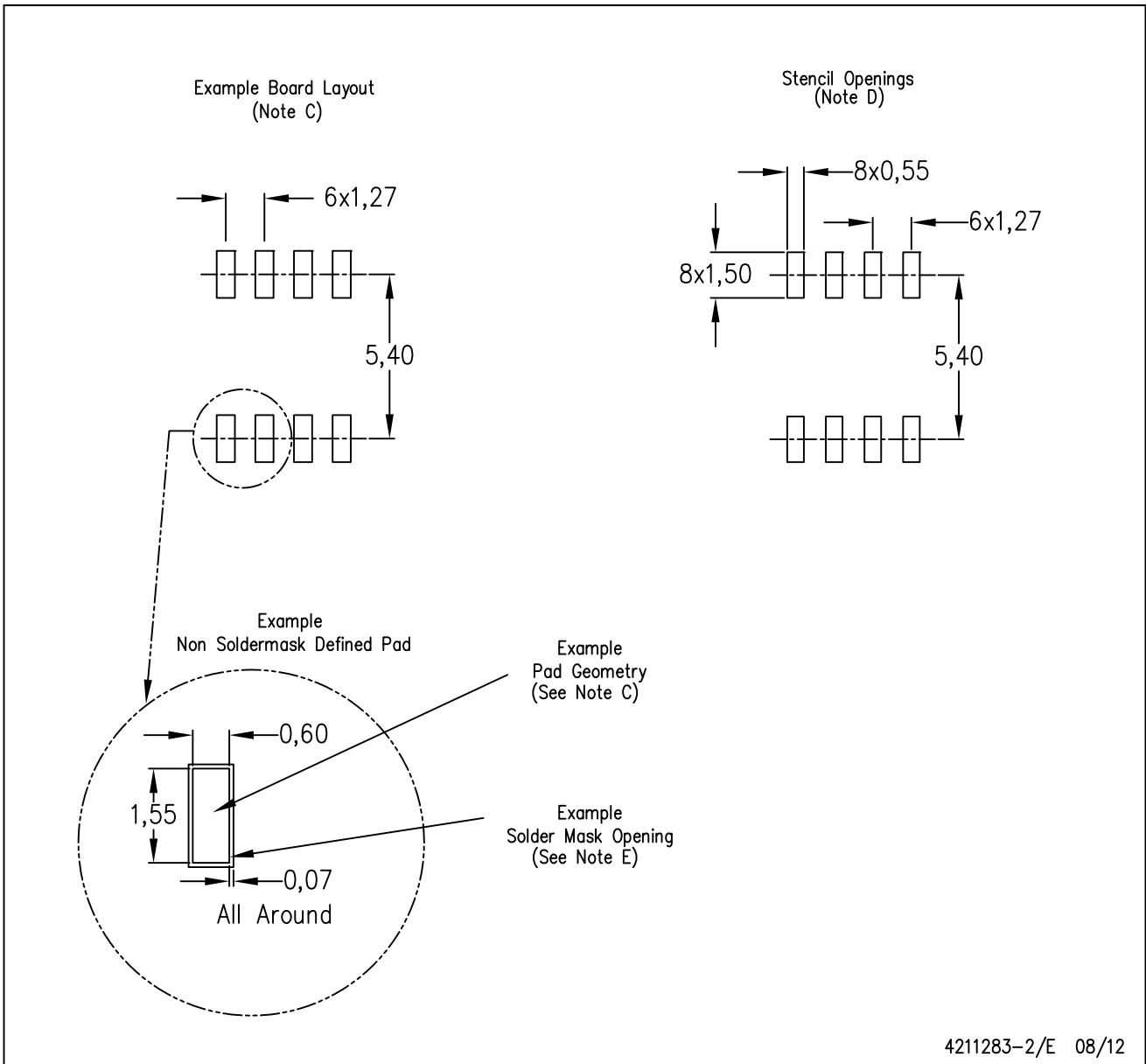


- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <<http://www.ti.com>>.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - Falls within JEDEC MO-187 variation AA-T

PowerPAD is a trademark of Texas Instruments.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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